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A Level Shifter With Almost Full Immunity to Positive dv/dt for Buck Converters

Yunzhe Yang, Mo Huang¹, Senior Member, IEEE, Sijun Du², Senior Member, IEEE, Rui P. Martins³, Life Fellow, IEEE, and Yan Lu⁴, Senior Member, IEEE

Abstract—High-frequency buck converters need a fast transition of switching nodes (high dv/dt). Such high dv/dt , especially the positive one, can cause malfunction of a conventional pulse-triggered active-coupled (PTAC) level shifter that is used to control the high-side NMOS switch. In this work, we first discuss the dv/dt immunity of conventional PTAC level shifters. Subsequently, we propose a new scheme to block the noise current during the dv/dt sequence, allowing an almost full immunity to the positive dv/dt . With this scheme, the maximum dv/dt is determined by how well the circuitry is protected from the overvoltage during the dv/dt sequence. We design a 20-V buck converter with this level shifter, fabricated in 180-nm BCD process. Experimental results show it works correctly under a 67-V/ns dv/dt .

Index Terms—DC-DC converter, level shifter, buck converter, dv/dt immunity.

I. INTRODUCTION

BUCK converter (Fig. 1) has a wide utilization in high-efficiency applications. Due to the high mobility, NMOS power transistors have a lower turn-on resistance than PMOS under the same chip area. Therefore, it is favorable to use an NMOS as the high-side switch (M_H). The gate driver of M_H is working in a floating-voltage (FV) domain (from $V_{SSH} = V_X$ to $V_{DDH} = V_X + V_{DR}$, where V_{DR} is the gate-drive voltage,

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Yunzhe Yang was with the State Key Laboratory of Analog and Mixed-Signal VLSI, the Department of Electrical and Computer Engineering (ECE), the Faculty of Science and Technology (FST), and the Institute of Microelectronics, University of Macau, Macau, China. He is now with the Department of Microelectronics, Delft University of Technology, 2628 CD Delft, Netherlands.

Mo Huang and Yan Lu are with the State Key Laboratory of Analog and Mixed-Signal VLSI, the Department of Electrical and Computer Engineering (ECE), the Faculty of Science and Technology (FST), and the Institute of Microelectronics, University of Macau, Macau, China (e-mail: mohuang@um.edu.mo).

Sijun Du is with the Department of Microelectronics, Delft University of Technology, 2628 CD Delft, The Netherlands.

Rui P. Martins is with the State Key Laboratory of Analog and Mixed-Signal VLSI, the Department of Electrical and Computer Engineering (ECE), the Faculty of Science and Technology (FST), and the Institute of Microelectronics, University of Macau, Macau, China, on leave from Instituto Superior Técnico, Universidade de Lisboa, 1049-001 Lisbon, Portugal.

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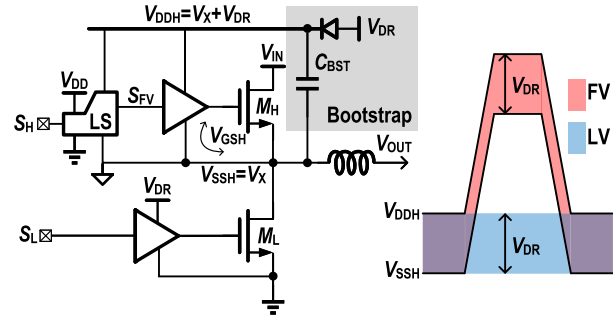


Fig. 1. Block diagram of a buck converter and voltage domains of its level shifter.

while V_X is the switching node from ground to supply voltage V_{IN}). Bootstrap circuit, consisting of a diode and a capacitor C_{BST} [1], is widely used to generate V_{DDH} that is V_{DR} higher than V_X . To turn M_H on and off, we need a level shifter (LS) to convert the control signal S_H from a low-voltage domain (LV, from ground to the control supply voltage V_{DD}) to the S_{FV} in FV domain. The level shifter design can be challenging in high-speed applications, where the short transient time of V_X leads to a high slew rate (dv/dt). The dv/dt can be even higher in high-voltage applications. A high dv/dt may lead to malfunction of the level shifter, as well as the converter.

There are three main categories of level shifters: 1) capacitive-coupled [1], [2], [3], [4], 2) voltage-triggered active-coupled [5], [6], [7], [8], [9], [10], and 3) pulse-triggered active-coupled (PTAC) level shifters [11], [12], [13], [14], [15], [16], [17]. A capacitive-coupled level shifter exhibits small power consumption but needs high-voltage capacitors. A voltage-triggered active-coupled level shifter has a simple circuitry, while consumes a large power. By contrast, a PTAC level shifter has the advantages of both small power consumption and no high-voltage capacitor, which is more popular in high-voltage applications [15].

The PTAC level shifter always uses a differential topology, utilizing an output latch to obtain rail-to-rail output signals, achieving a small power consumption and propagation delay. However, the conventional PTAC level shifter has a high risk of output logic failure under a large common-mode noise current I_{NOISE} from a high positive dv/dt (V_X transitions from ground to V_{IN} in a short time), as explained in Section II. By contrast, a negative dv/dt (V_X transitions from V_{IN} to ground) has little harm on PTAC level shifter, as discussed in Section III-D. Therefore, most of the previous literatures investigated the topology of the PTAC level shifter that can resist a high positive dv/dt , a.k.a. to obtain a good

TABLE I
THE dv/dt ISSUE OF CONVENTIONAL PTAC LEVEL SHIFTER

	Safety condition	Required transistor sizes
Signal phase	$I_{\text{SIG}} > I_{\text{SIG,TH}}$	Large M_{1A} , M_{1B} , and small M_{4A} , M_{4B}
Noise phase	$I_{\text{NOISE}} < I_{\text{NOISE,TH}}$	Small M_{1A} , M_{1B} , and large M_{4A} , M_{4B}

immunity to positive- dv/dt . For instance, [12] added shunt branches, and [14] added bypass transistors to reduce the I_{NOISE} within the dv/dt sequence. But their dv/dt immunity was improved with a higher circuit complexity, or an increased number of high-voltage MOSFETs. Reference [15] proposed a dual-interlock level shifter that desensitized the output stage, but increased the propagation delay. Furthermore, these designs may still malfunction under a very high dv/dt .

To address these issues and further improve the immunity to positive dv/dt , we propose a scheme that blocks the I_{NOISE} within the dv/dt sequence. This facilitates an almost full immunity, which means that in theory, the proposed level shifter functions correctly under an I_{NOISE} from infinitely large positive dv/dt . Its maximum allowable dv/dt is only determined by how well the protection diodes can protect the transistors from overstressing, as discussed in Section III-B. We organize this paper as follows: Section II reviews the previous PTAC level shifters and discusses their maximum dv/dt immunity. Section III presents the working principles and implementations of the proposed level shifter, and discusses its limitations. Section IV shows the simulation and measurement results, and a comparison with previous works. Section V draws the conclusions.

II. REVIEW OF PREVIOUS PTAC LEVEL SHIFTERS

A. Working Principles of the Conventional Level Shifter When $Dv/Dt = 0$

Fig. 2(a) shows the schematic of a conventional PTAC level shifter. The LV Pulse Generator outputs pulse V_{1A} and V_{1B} from the rising and falling edge of the input signal S_H , respectively. M_{1A} and M_{1B} are differential input high-voltage MOSFETs in LV domain, each with an output parasitic capacitance C_{P1} (to ground). Two inverters, M_{4A} , M_{5A} and M_{4B} , M_{5B} make up a latch. The outputs of the latch are V_{OA} and V_{OB} , with parasitic capacitance C_A and C_B (to $V_{SSH} = V_X$), respectively. Differential output buffers are used to ensure the same load capacitance of the two inverters. The output buffers generate a non-inverting output signal OUT_A and inverting signal OUT_B . Transistors M_{2A} , M_{3A} , M_{2B} , and M_{3B} (equal size) are current mirrors to copy the input currents from LV domain to FV domain.

We first review the working principles of this PTAC level shifter under a positive-edge input S_H , when $dv/dt = 0$. We define this period as signal phase. Fig. 2(a) includes the signal currents within the signal phase, and the transient waveforms are given in Fig. 2(c). It starts with $V_{OA} = "0"$ and $V_{OB} = "1"$. I_{CA} is the current charging C_A :

$$I_{CA} = I_{OA} - I_{4B} + I_{5B}, \quad (1)$$

where I_{OA} , I_{4B} and I_{5B} are current from M_{3A} , M_{4B} and M_{5B} , respectively. Note that we should ensure $I_{CA} > 0$ before the latch outputs flip completely in the signal phase, otherwise the latch will be locked in the state $V_{OA} = "0"$ and $V_{OB} = "1"$.

At S_H 's rising edge t_1 , V_{1A} turns on M_{1A} , outputting a current I_{SIG} which is mirrored to I_{OA} through the current mirror M_{2A} - M_{3A} . Most I_{OA} is injected to C_A at t_1 , and V_{OA} increases. From t_1 to t_2 , V_{DS} of M_{4B} increases due to the I_{CA} injection, and I_{4B} increases. V_{OB} almost has no change, and $I_{5B} = 0$. From t_2 to t_3 , V_{OA} becomes sufficiently high to turn on M_{4A} , discharging C_B and decreasing V_{OB} . I_{OA} decreases because of an increasing V_{OA} , considering the channel length modulation effect of M_{3A} . Then I_{CA} is decreasing. I_{5B} is around 0. From t_3 to t_4 , because of the V_{OB} decreasing, I_{5B} rises and I_{4B} falls, making I_{CA} raises again. This pulls V_{OA} up and V_{OB} down, and finally flips the outputs of the latch.

Clearly, I_{CA} achieves the minimum value at t_3 , where M_{3A} works in saturation region due to the relatively low V_{OA} . Therefore, $I_{OA}(t_3)$ should well copy $I_{\text{SIG}}(t_3)$, $I_{OA}(t_3) = I_{\text{SIG}}(t_3)$. To make $I_{CA}(t_3) > 0$, we need to guarantee $I_{OA}(t_3) > I_{4B}(t_3)$ from equation (1), because $I_{5B}(t_3) \approx 0$. That is:

$$I_{\text{SIG}}(t_3) = I_{OA}(t_3) > I_{4B}(t_3) = I_{\text{SIG,TH}}, \quad (2)$$

where $I_{\text{SIG,TH}}$ is the threshold I_{SIG} to flip the latch, at t_3 .

Clearly, to meet (2), we should choose large I_{SIG} (W_1) and small I_{4B} (W_4), where W_1 and W_4 are channel width of M_{1A} (and M_{1B}) and M_{4A} (and M_{4B}), respectively.

B. Dv/Dt Issue of the Conventional Level Shifter

Since the C_{BST} in Fig. 1 holds an almost constant voltage difference between V_{DDH} and V_X , $dV_{\text{DDH}}/dt = dv/dt$. As shown in Fig. 2(b), the parasitic capacitance C_{P1} on M_{1A} and M_{1B} generates common-mode I_{NOISE} within a dv/dt sequence:

$$I_{\text{NOISE}} = C_{P1} \cdot dv/dt. \quad (3)$$

Part of I_{NOISE} is mirrored to I_{OB} and I_{OA} , leading to possible false output of the latch. Hence we define the period of the dv/dt sequence as the noise phase.

Fig. 2(d) shows how different dv/dt magnitudes affect the output of the level shifter. Initial state is $V_{OA} = "1"$ and $V_{OB} = "0"$ at t_5 , after the operation of the previous signal phase. When dv/dt is small, a small I_{OB} mirrored from I_{NOISE} pulls V_{OB} up to some extent, and the V_{OB} rise could pull V_{OA} down to a smaller value. But such a small change does not flip the output of the level shifter.

However, the I_{NOISE} from a large dv/dt can pull V_{OB} up greatly, and flip OUT_B at t_6 . Subsequently, the OUT_B flipping can either maintain or flip back (as a glitch). Both glitch and flipping are harmful for buck converters.

To prevent the V_{OB} from crossing the threshold voltage at t_6 , we should guarantee the C_B current $I_{CB}(t_6) < 0$. With M_{5A} turned off and M_{4A} turned on at t_6 , we write:

$$I_{CB}(t_6) = I_{OB}(t_6) - I_{4A}(t_6) \approx I_{\text{NOISE}} - I_{4A}(t_6), \quad (4)$$

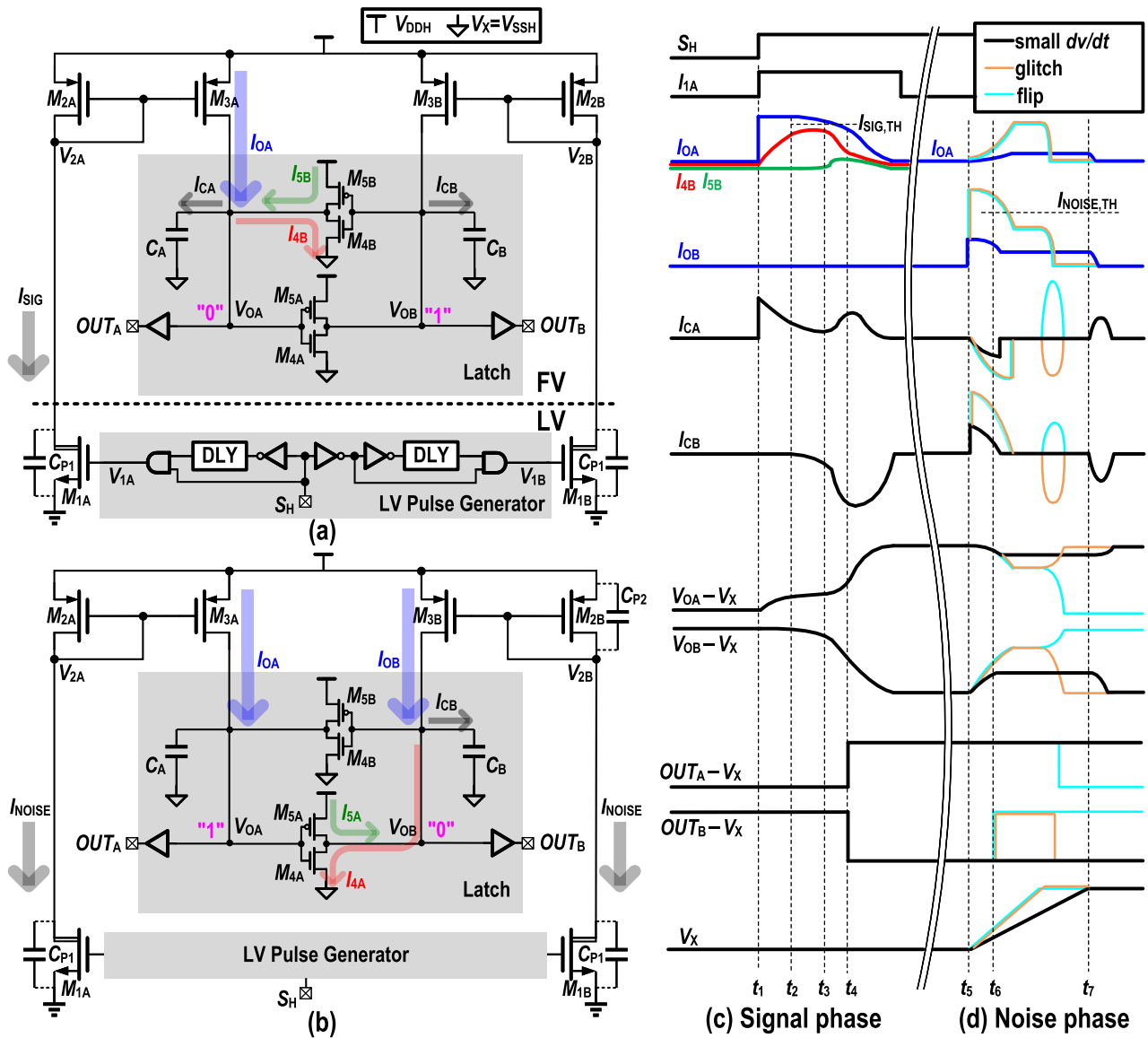


Fig. 2. (a) Schematic of a conventional PTAC level shifter and signal currents within the signal phase (from t_1 to t_4), (b) noise currents within noise phase (from t_5 to t_7), (c) transient waveforms with a positive-edge input signal, within the signal phase, and (d) transient waveforms within the noise phase.

where I_{4A} is the current of M_{4A} . Substitute I_{NOISE} with (3) and make (4) < 0 , we have:

$$dv/dt < \frac{1}{C_{P1}} I_{4A}(t_6) = \frac{1}{C_{P1}} I_{NOISE,TH}, \quad (5)$$

where $I_{NOISE,TH}$ is the threshold value of I_{NOISE} to cause a false output of the level shifter.

Obviously, we could improve the dv/dt immunity by reducing C_{P1} or increasing I_{4A} (W_4), which means reducing the size of M_{1A} (and M_{1B}) and increasing the size of M_{4A} (and M_{4B}). However, both ways may contradict equation (2) for the signal phase. Thus, the dv/dt immunity of the conventional level shifter is limited.

Table I summarizes the dv/dt issue of the conventional PTAC level shifter. The safety condition in the signal phase requires large M_{1A}, M_{1B} , and small M_{4A}, M_{4B} sizes, while that in the noise phase needs small M_{1A}, M_{1B} , and large $M_{4A},$

M_{4B} . Clearly, the required transistor sizes of the two phases contradict each other.

Work from [12] improved the immunity to dv/dt with shunt branches, significantly reducing the currents I_{OA} and I_{OB} injected into the latch under a dv/dt . However, the improvement is limited, since the noise current is not completely removed. A possible malfunction could take place under a high dv/dt . Consequently, it is more attractive if a new topology can block I_{NOISE} completely and achieve a full immunity to dv/dt .

III. WORKING PRINCIPLES AND IMPLEMENTATIONS OF THE PROPOSED DESIGN

A. Working Principles

Fig. 3 displays the high-side switch turning on waveforms of a buck converter in Fig. 1. Time interval t_1 - t_2 is the rising delay of the level shifter. Interval t_2 - t_3 is the delay between the rising edge of S_{FV} and V_{GSH} rising to its Miller Plateau

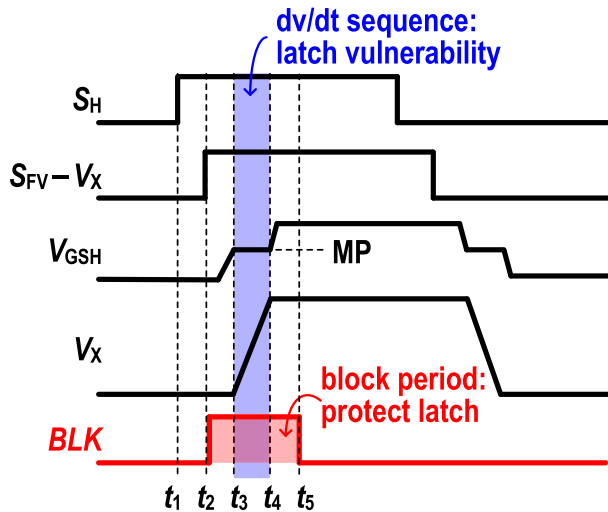


Fig. 3. Switching waveforms of a buck converter, and a possible way to obtain the full immunity to positive dv/dt .

(MP). After that, the dv/dt sequence occurs within t_3 - t_4 , where the triggered I_{NOISE} makes the level shifter vulnerable.

If we can completely block I_{NOISE} from t_3 to at least t_4 (with BLK signal), the level shifter output sees no common-mode noise current, and thus should resist an infinitely large dv/dt , (full immunity to positive dv/dt). Therefore, the rising edge of BLK should be generated after the rising edge of S_{FV} (t_2), and before the dv/dt sequence (t_3). This should be implementable, since interval t_2 - t_3 usually lasts several nanoseconds, consisting of the delay between S_{FV} and V_{GSH} , and the time interval from V_{GSH} rising to its MP. Subsequently, BLK should be ended shortly after the dv/dt sequence (t_5), enabling I_{SIG} again.

Fig. 4 (a) presents the schematic of the proposed level shifter, based on the work from [12]. The shunt branches (M_{P2A} , M_{N2A} , M_{N3A} , M_{P2B} , M_{N2B} , and M_{N3B}) are used to equalize the delay of the rising and falling edges. Resistors R_{1A} , R_{1B} , R_{2A} , and R_{2B} prevent the current mirror misconducting during non-working periods. Furthermore, we add the BLK generator (consisting of a delay chain DLY_1 , an inverter and an AND gate), blocking transistors (M_{P3A} , M_{P5A} , M_{P3B} , and M_{P5B}), and diode D_{1A} and D_{1B} for overvoltage protection [15]. We implement DLY_1 with an inverter chain.

Fig. 4 (b) explains the working principles of the proposed design. The BLK generator detects the positive edge of OUT_A , and generates a pulse signal BLK . The BLK turns off the M_{P3A} , M_{P5A} , M_{P3B} , and M_{P5B} synchronously, nulling the current I_{OA} and I_{OB} , or blocking the noise current from the parasitic capacitors of HV MOSFETs M_{N1A} and M_{N1B} . Therefore, the dv/dt sequence does not cause a malfunction. The waveforms without the block period are also given in Fig. 4 (b) for comparison.

We control the pulse width of BLK by carefully designing the delay of delay chain DLY_1 . Its pulse width should be determined by the working frequency and load range of the buck converter. If the buck converter works in a higher frequency, we can design a narrower pulse width for BLK .

Note that a very large dv/dt still causes some V_{OA} and V_{OB} variations. This is because the capacitance between V_{OA} , V_{OB} and ground (C_{PA} , C_{PB} in Fig. 4 (a)) should be charged by C_A and C_B , within the positive dv/dt sequence. But due to the small value of C_{PA} , C_{PB} , the variations would be too small to flip the latch.

B. Maximum Dv/Dt Immunity of the Proposed Level Shifter

Although blocking I_{NOISE} can theoretically protect the latch from an infinitely large dv/dt sequence, such dv/dt may still be unsafe for the proposed level shifter. As shown in Fig. 5 (a), we use the R_{P1A} and R_{N1A} to represent the R_{DS} of M_{P1A} and M_{N1A} , respectively. The DC voltage of V_{2A} is V_{DDH} over the resistive divider of R_{P1A} and R_{N1A} . In the steady state, M_{N1A} is turned off, and hence R_{N1A} is large and V_{2A} is close to V_{DDH} . When a large dv/dt occurs, the large I_{NOISE} flows through the low-impedance capacitive divider path (C_{P2} and C_{P1}). Charging C_{P2} with the I_{NOISE} leads to an instantaneous increase in V_{SD} of M_{P1A} ($= V_{DDH} - V_{2A}$), as shown in Fig. 5 (a) and (c). The peak V_{SD} value at a large dv/dt is approximately equal to the V_{DDH} step ($= V_{IN}$) over the capacitive divider:

$$V_{SD,PEAK} \propto \frac{C_{P1}}{C_{P1} + C_{P2}} V_{IN}. \quad (6)$$

Once V_{IN} is not high and C_{P2} is large, the instantaneous V_{2A} (or V_{2B}) does not overstress M_{P1A} , M_{P2A} and M_{P4A} (nor M_{P1B} , M_{P2B} , and M_{P4B}). In this sense, the level shifter has “truly” full immunity to positive dv/dt . Nevertheless, if V_{IN} is high or C_{P2} is relatively small, a very large I_{NOISE} can instantly charge C_{P2} and then overstress the transistors (the “ V_{2A} no D_{1A} ” case as shown in Fig. 5 (c)).

To address this, diodes D_{1A} and D_{1B} are added to clamp V_{2A} and V_{2B} to V_X , and thus circumvent the overstress issue, as shown in Fig. 5 (b). In this scenario, the diode conducts part of I_{NOISE} , reducing the peak $V_{SD,PEAK}$ from equation (6). However, it is possible that the diode current I_D is instantaneously smaller than I_{NOISE} , making the diodes clamp V_{2A} to an instantaneously lower value that is still risky of overvoltage (the “ V_{2A} small D_{1A} ” case). Therefore, we should choose a large diode that can conduct sufficient I_{NOISE} during a dv/dt sequence (the “ V_{2A} large D_{1A} ” case).

In sum, the maximum dv/dt immunity of the proposed design is determined by protection diodes. With sufficiently large protection diodes, the proposed scheme can theoretically resist an infinitely large dv/dt , which is significantly improved from the previous works. We regard it as “almost” full immunity to positive dv/dt .

C. Possible Drawback and Solution

The possible drawback of this scheme is that the I_{SIG} may be blocked by the BLK signal as well. This prohibits the S_H signal transmission to the high-side switch through the level shifter during the block period (BLK enable in Fig. 3).

Fortunately, for most buck converters, the S_H transmission during the block period is not needed. To our best knowledge, the possible exception is the design that precisely controls

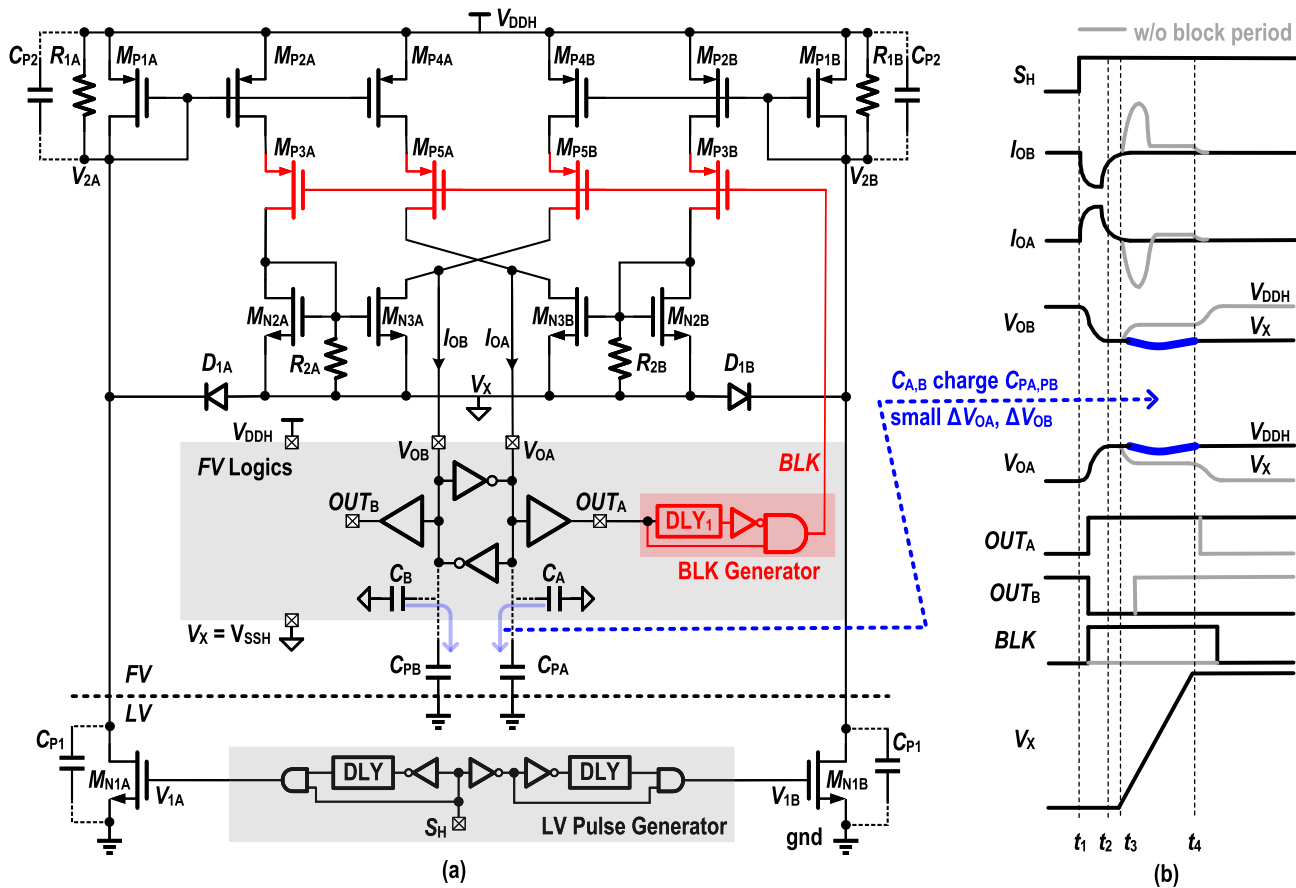


Fig. 4. (a) Schematic and (b) transient waveforms of the proposed level shifter.

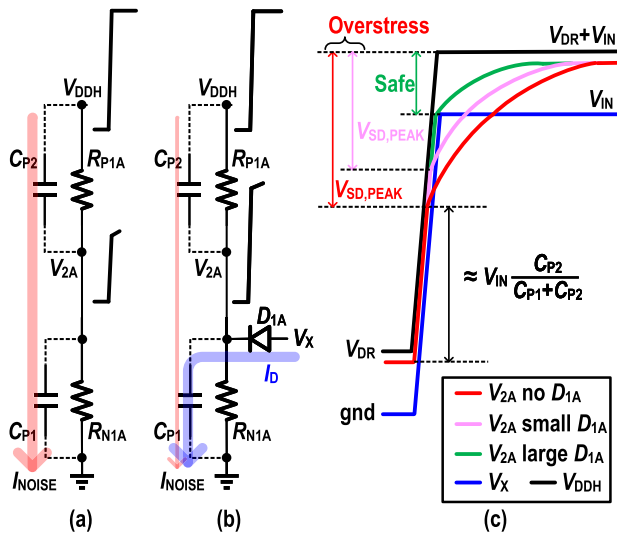


Fig. 5. I_{NOISE} conduction path (a) without and (b) with the protection diodes. Only show left-hand branch of the level shifter for simplicity. (c) V_{2A} waveforms within a dv/dt sequence.

the dv/dt value, such as in [18], where multiple S_H signals are transmitted during a dv/dt sequence. However, the precise dv/dt control schemes usually have stringent requirements on the delay of the transmission path. This makes the close-loop dv/dt control between the FV and LV domains not acceptable. Therefore, a possible and reasonable alternate is to implement the closed-loop control in FV, without using the level shifter,

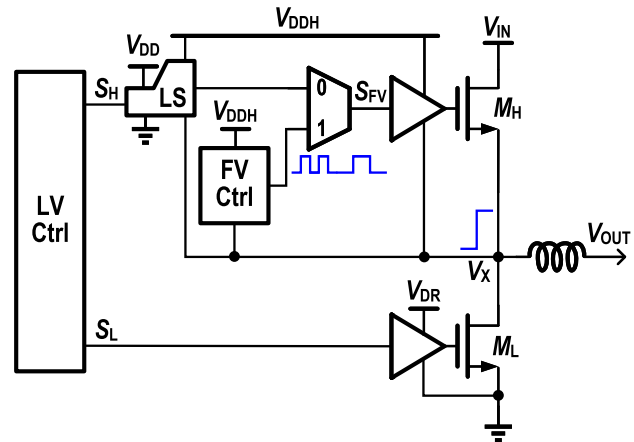


Fig. 6. A possible solution to control M_H during a dv/dt sequence, compatible to the proposed scheme.

as shown in Fig. 6 [19], [20]. This removes the delay of the level shifter. Clearly, this scheme is fully compatible with the proposed level shifter.

D. Immunity to Negative Dv/Dt

A negative dv/dt triggers a negative I_{NOISE} that is conducted to V_{DDH} through the body diode of M_{P1A} and M_{P1B} . Therefore, the I_{NOISE} is not mirrored to the latch. That is why converters usually have a much higher tolerance to a negative dv/dt .

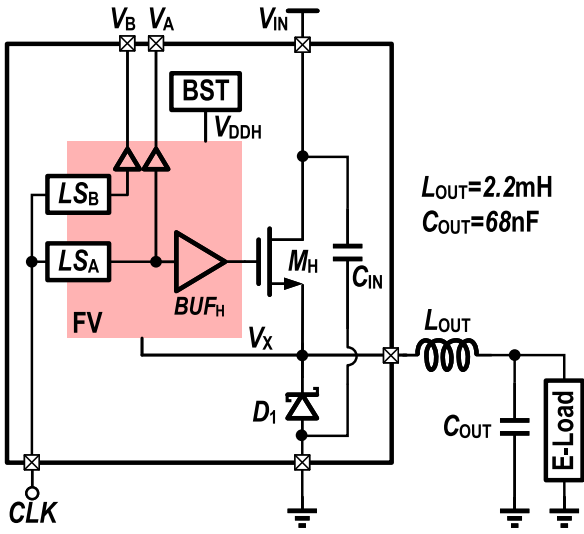
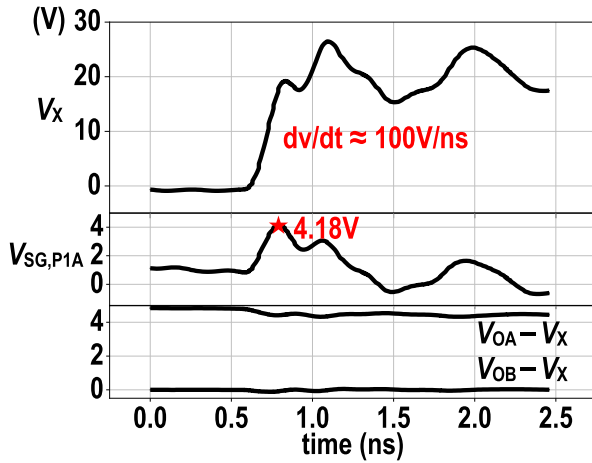


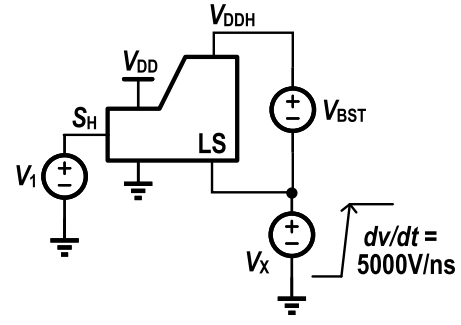
Fig. 7. Block diagram of the DUT.

Fig. 8. Post-layout simulation results when $dv/dt \approx 100V/ns$.

In fact, too large negative dv/dt could cause reliability issue as well. With a very large negative I_{NOISE} , V_{2A} and V_{2B} are pulled higher to conduct more I_{NOISE} . This may overstress D_{1A} and D_{1B} . Additional protection circuits should be added.

E. Implementations

Fig. 7 is the block diagram of the design under test (DUT). An asynchronous buck converter generates the dv/dt . The switching frequency is 500KHz. M_H is the power switch, D_1 is the asynchronous diode. The M_H , D_1 , and bootstrap (BST) block are integrated. As widely used in buck converter, we integrate an on-chip input capacitor C_{IN} to provide a low-impedance AC path from V_{IN} to ground, filtering out the high-frequency glitches on V_{IN} . The value of C_{IN} implemented is 42pF, occupying a silicon area of 0.112mm². We integrate the proposed level shifter (LS_A), and also a level shifter (LS_B) using the topology in [12], as a baseline design for comparison. V_A and V_B are their outputs, respectively. We observe the V_A and V_B after on-chip buffers. Only the LS_A is used to control M_H , in case the malfunction of LS_B under a high dv/dt .

Fig. 9. Testbench of the proposed level shifter under $dv/dt = 5000V/ns$.

To measure the robustness of the level shifters under different dv/dt , we predesign two dv/dt s.

To verify the dv/dt immunity of the proposed scheme, it is desirable to design the DUT buck converter with a high dv/dt . However, the high dv/dt design is challenging. From [21], the dv/dt of a buck converter is:

$$dv/dt = \frac{g_{FS}(V_{GS} - V_{MP})}{C_{OSS_HS} + C_{OSS_LS}}, \quad (7)$$

where g_{FS} is the transconductance of the M_H , V_{MP} is the beginning voltage of the MP, C_{OSS_HS} and C_{OSS_LS} are the output capacitances of M_H and D_1 , and V_{GS} is the gate-source voltage of the M_H in the Miller Plateau calculated as:

$$\frac{dV_{GS}}{dt} = \frac{V_{DR} - V_{GS}}{R_G C_{ISS_HS}} - \frac{g_{FS} C_{RSS_HS} (V_{GS} - V_{MP})}{C_{ISS_HS} (C_{OSS_HS} + C_{OSS_LS})}, \quad (8)$$

where R_G is the output resistance of the gate drive buffer BUF_H , and C_{RSS_HS} and C_{ISS_HS} are the reverse transfer and input capacitance of M_H .

Equation (7) and (8) indicate that $dv/dt = 0$ at the beginning of the MP, and increases to the maximum value after some time. Increasing the input voltage V_{IN} may allow a larger dv/dt , such as in [15], by extending the time duration of the MP.

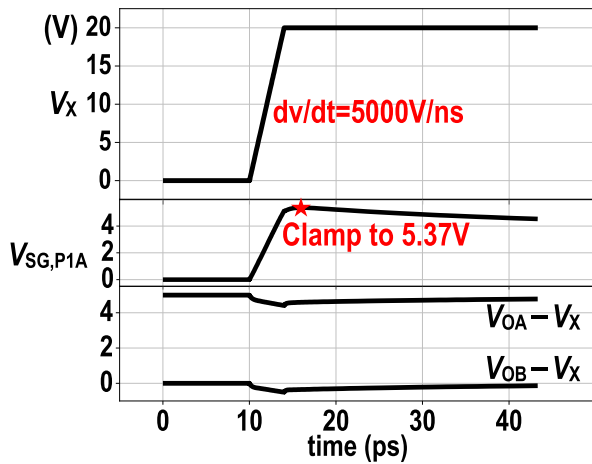
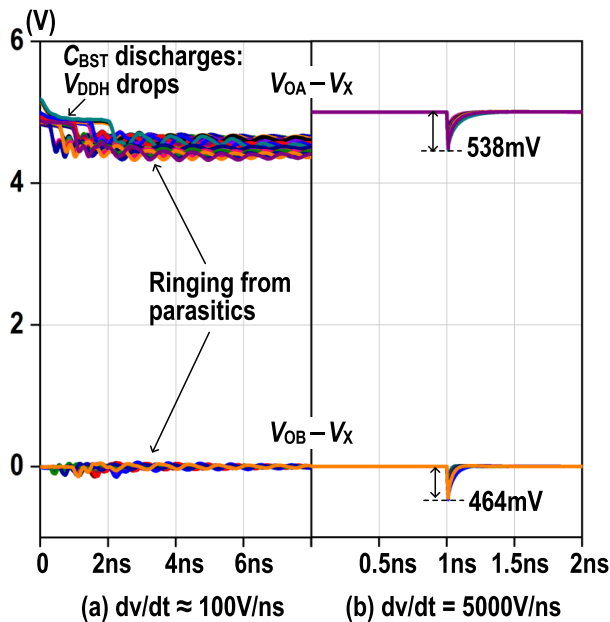
However, the DUT is designed with devices only sustaining 20-V V_{IN} in this work. Therefore, we should increase dv/dt by reducing C_{OSS_HS} and C_{OSS_LS} as indicated in (7). Hence, we use a Schottky diode D_1 as the low-side switch, which has a smaller C_{OSS_LS} than that of a high-voltage MOSFET that conducts the same current. Meanwhile, we choose a small M_H size to minimize the C_{OSS_HS} .

Finally, we control the slew rate of V_{GS} for the maximum dv/dt , by using a strong BUF_H . However, even though we intentionally increase the dv/dt , the maximum value in post-layout simulation is only around 100V/ns, with parasitics included.

IV. SIMULATION AND MEASUREMENT RESULTS

Fig. 8 shows the post-layout simulation results under the implemented 100V/ns dv/dt , from DUT in Fig. 7. Under the protection of D_{1A} and D_{1B} , the peak $V_{SG,P1A}$ is 4.18V. Voltage $V_{OA} - V_X$ and $V_{OB} - V_X$ have small fluctuations. But the fluctuations do not cause a false output.

However, the dv/dt from an implemented buck converter is not high enough to verify the claimed ‘‘almost full immunity’’ to positive dv/dt . Therefore, we use another testbench as


 Fig. 10. Post-layout simulation results when $dv/dt = 5000V/ns$.

 Fig. 11. Post-layout simulation results of $V_{OA}-V_X$ and $V_{OB}-V_X$ under different PVT conditions when (a) $dv/dt \approx 100V/ns$ (TB is Fig. 7), and (b) $dv/dt = 5000V/ns$ (TB is Fig. 9).

shown in Fig. 9. The level shifter input S_H is connected to a DC voltage, while the bootstrap capacitor is replaced by a DC voltage source V_{BST} . We use an ideal voltage pulse signal V_X with 5000-V/ns slew rate (rise to 20V within 4ps). Fig. 10 shows the post-layout simulation results. Like in the 100V/ns- dv/dt scenario, the output logics are correct under the 5000-V/ns dv/dt , while the protection circuits clamp the peak $V_{SG,P1A}$ within the 5.5V maximum V_{SG} voltage.

Fig. 11 verifies the proposed design under different PVT conditions, where the TT, SS, FF corners, $-40^\circ C$, $27^\circ C$ and $105^\circ C$ temperatures, 10V, 15V and 20V V_{IN} are included. Fig. 11 (a) uses the testbench (TB) in Fig. 7, while Fig. 11 (b) uses the TB in Fig. 9. As observed in Fig. 11 (a), under a 100-V/ns dv/dt , $V_{OA}-V_X$ decreases because of the V_{DDH} drop from the C_{BST} discharging. And $V_{OA}-V_X$ and $V_{OB}-V_X$ show ringings due to the parasitics included in DUT. Clearly, the dv/dt does not malfunction the level shifter. From Fig. 11 (b), the level shifter outputs have around 500-mV undershoot under

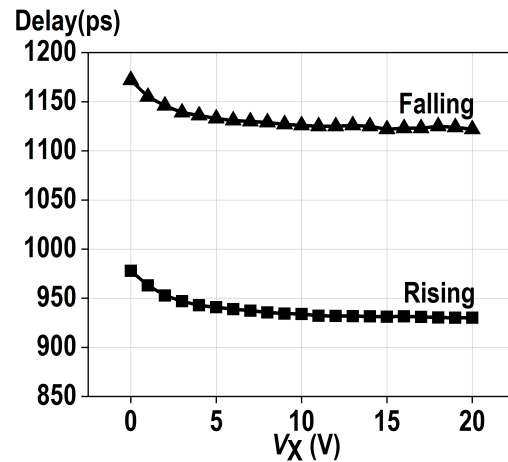


Fig. 12. Simulated delay of the proposed level shifter of rising edge input and falling edge input.

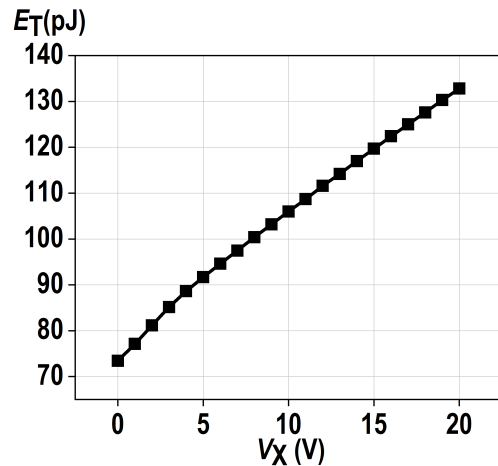


Fig. 13. Simulated energy consumption of the proposed level shifter.

the 5000-V/ns dv/dt , as discussed in Fig. 4. But the level shifter output is functionally correct.

Fig. 12 shows the post-layout simulation results of the delay of the level shifter. Delay of both rising and falling edges are around 1ns. The variation of the delay from 0 to 20V V_X is small. Although we insert couples of switches to the signal propagation paths to block the I_{NOISE} during the dv/dt sequence, the delay only increases slightly, and is comparable to the conventional level shifters.

Fig. 13 shows the post-layout simulation results of energy consumption in one transition (E_T). Compared to conventional level shifters, the additional power loss of the proposed design mainly comes from DLY_1 . This power loss is around 16% as shown in the power loss breakdown in Fig. 14, when $V_{IN} = 20V$. Such power loss can be further reduced by using low-power delay chain design.

Fig. 15 (a) shows the post-layout simulation results of the delay between the start time of dv/dt (t_3 in Fig. 3), and the rising edges of BLK ($t_{BLK,RISE}$), under different corners. As seen, in all corners simulated, the BLK rising edge takes place at least 1ns before t_3 . Fig. 15 (b) shows the simulated BLK pulse width, which covers the whole dv/dt sequence without blocking I_{SIG} too long. These verify the robustness of the BLK generator.

TABLE II
COMPARISON WITH PREVIOUS WORKS

	Year	Process(μm)	Area(mm^2)	V_{IN} (V)	Delay(ns)	E_{T} (pJ)	Sim. dv/dt (V/ns)	Meas. dv/dt (V/ns)
[1]	2015	0.5	N/A	40	2	160	40	N/A
[12]	2016	0.18	0.005	20	0.37	27.6	30	N/A
[2]	2018	0.18	0.00735	50	1.45	4.1	100	6
[22]	2018	0.5	N/A	80	1.618	N/A	50	N/A
[13]	2019	0.18	0.018	50	0.53	30.3	200	N/A
[3]	2021	0.18	0.0096	200	0.67	8.1	200	N/A
[4]	2023	0.5	0.051	50	1.26	27.3	200	56
This work (baseline)	2023	0.18	0.0045	20	1.02	105	8	<15
This work (proposed)			0.0094	20	1.17	133	>5000	67

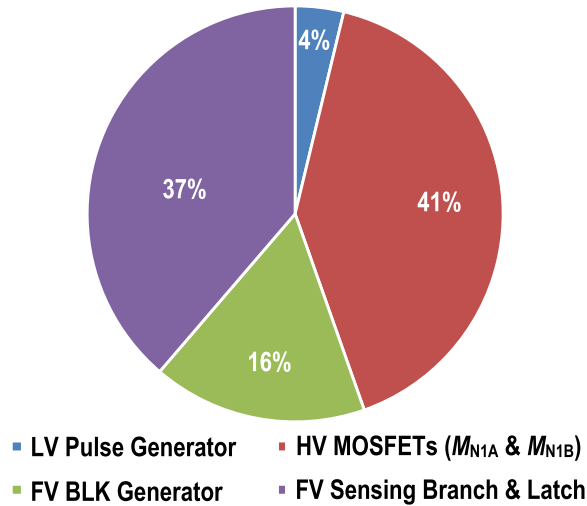


Fig. 14. Power loss breakdown of the proposed level shifter.

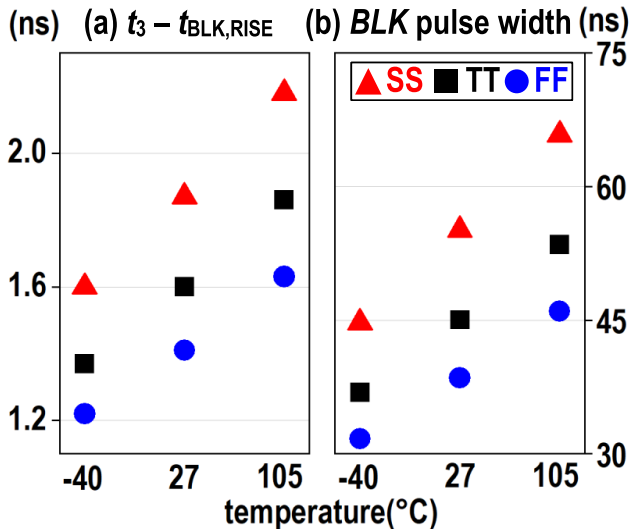


Fig. 15. Post-layout simulation of BLK signal timings under different corners: (a) delay between the dv/dt sequence and the rising edge of BLK ($t_{\text{BLK,RISE}}$), and (b) BLK pulse width.

We used a $0.18\text{-}\mu\text{m}$ Bipolar-CMOS-DMOS(BCD) process to fabricate the chip, and the maximum input voltage of the DUT buck converter is 20V. Fig. 16 shows the photo of the PCB, and the micrograph of the chip. We used chip-on-board (COB) packaging to connect the chip and PCB. The silicon area of LS_A and LS_B are around $9400\mu\text{m}^2$ and $4500\mu\text{m}^2$,

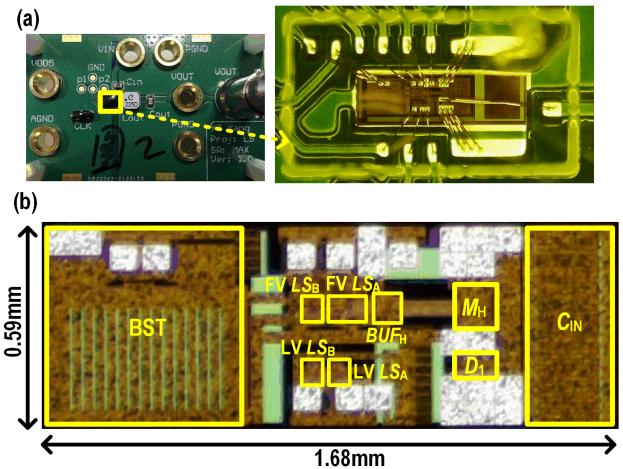


Fig. 16. (a) PCB photos, and (b) chip micrograph.

respectively. The additional area of LS_A comes from the BLK generator.

To capture the high frequency signals, we use an oscilloscope Keysight DSO-X 6004A (6GHz), an active differential probe Keysight 1134A (7GHz) and an attenuator Keysight 2880A (20dB). They can detect signal change in several hundreds of picoseconds.

Fig. 17 shows the measured waveforms of the buck converters with the proposed and baseline level shifter. We calculate the dv/dt value from the V_X waveform, using the calculator of the oscilloscope. The achieved maximum dv/dt is 67V/ns , lower than the simulated result. As observed, the proposed level shifter generates the correct output when the dv/dt is both 67V/ns and 15V/ns . We observe ringing on V_A and V_B within the dv/dt sequence. This stems from the resonance of V_A (or V_B) output parasitic inductance and the C_{BST} . But we tell that the LS_A output is correct, otherwise the incorrect V_X flipping should be observed.

Table II compares the proposed design with previous works and the baseline design. With a comparable silicon area, power consumption, and propagation delay, the proposed design achieves both the highest simulated and measured immunity to positive dv/dt . The proposed I_{NOISE} blocking scheme should achieve an even higher measured dv/dt if we implement the converter with a high-voltage process.

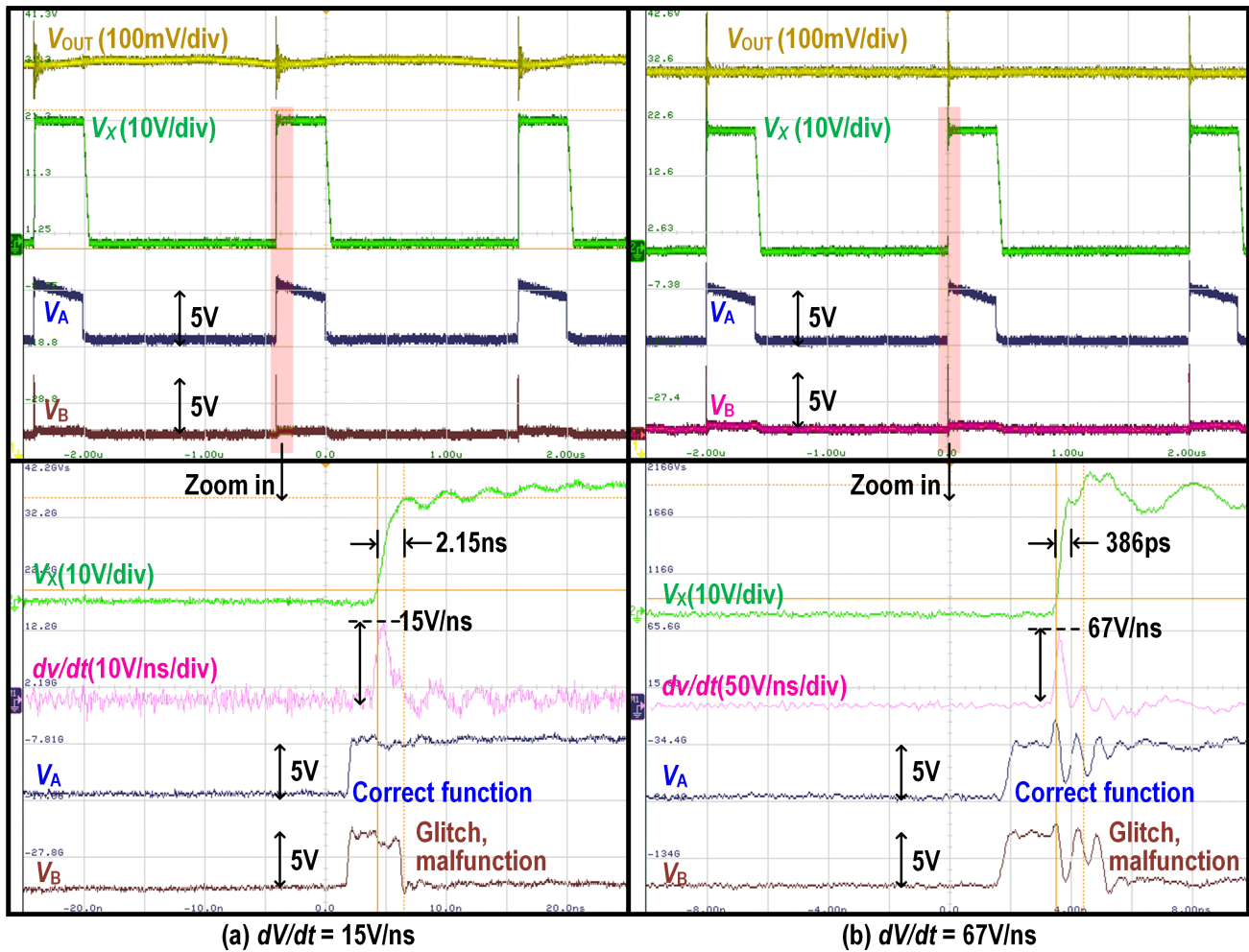


Fig. 17. Measured steady-state waveforms (a) with a 15V/ns, and (b) a 67V/ns dv/dt .

V. CONCLUSION

This article presented a PTAC-based level shifter that blocked the common-mode noise current during the positive dv/dt sequence. This achieved an almost full immunity to positive dv/dt , with the maximum dv/dt determined by how well the diodes can protect the transistors from overstressing. This scheme is compatible with a buck converter. The simulation results confirmed at least an immunity to 5000-V/ns dv/dt , while the silicon results exhibited 67V/ns.

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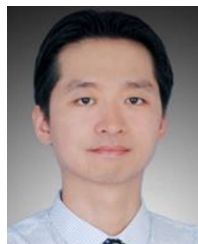
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Yunzhe Yang received the B.Eng. degree from Tianjin University, Tianjin, China, in 2020, and the M.Sc. degree from the University of Macau, Macau, China, in 2023. He is currently pursuing the Ph.D. degree in microelectronics with the Electronic Instrumentation Laboratory, Delft University of Technology, Delft, The Netherlands.

His research interests include thermoelectric energy harvesting, new topology of DC/DC converters, and GaN driving techniques.



Mo Huang (Senior Member, IEEE) received the B.Sc., M.Sc., and Ph.D. degrees in microelectronics and solid-state electronics from Sun Yat-sen University, Guangzhou, China, in 2005, 2008, and 2014, respectively.

From 2008 to 2014, he was an IC Design Engineer and the Project Manager with Rising Micro-electronic Ltd., Guangzhou. From 2015 to 2016, he was a Post-Doctoral Fellow with the State Key Laboratory of Analog and Mixed-Signal VLSI (AMSV), University of Macau, Macau, China.

From 2017 to 2019, he was with the School of Electronic and Information Engineering, South China University of Technology, Guangzhou, as an Associate Professor. He is currently an Assistant Professor with AMSV and the Institute of Microelectronics, University of Macau. His research interests include power management integrated circuits and systems.

Dr. Huang has served as a technical program committee member of multiple conferences. He was a recipient of the ISSCC 2017 Takuo Sugano Award for Outstanding Far-East Paper. He has been serving as an Associate Editor for *Microelectronics Journal* since 2021.



Sijun Du (Senior Member, IEEE) received the B.Eng. degree (Hons.) in electrical engineering from University Pierre and Marie Curie (UPMC), Paris, France, in 2011, the M.Sc. degree (Hons.) in electrical and electronics engineering from Imperial College, London, U.K., in 2012, and the Ph.D. degree in electrical engineering from the University of Cambridge, Cambridge, U.K., in January 2018.

He was with Laboratoire d'Informatique de Paris 6 (LIP6), UPMC, and then he was a Digital IC Engineer in Shanghai, China, from 2012 to 2014. He was a Summer Engineer Intern with Qualcomm Technology Inc., San Diego, CA, USA, in 2016. He was a Visiting Scholar with the Department of Microelectronics, Fudan University, Shanghai, in 2018. He was a Post-Doctoral Researcher with the Berkeley Wireless Research Center (BWRC), Department of Electrical Engineering and Computer Sciences (EECS), University of California at Berkeley, Berkeley, CA, USA, from 2018 to 2020. In 2020, he joined the Department of Microelectronics, Delft University of Technology (TU Delft), Delft, The Netherlands, where he is currently an Assistant Professor.



Rui P. Martins (Life Fellow, IEEE) received the Ph.D. degree in electrical engineering and computers from the Department of Electrical and Computer Engineering, Instituto Superior Técnico, University of Lisbon, Lisbon, Portugal, in 1992.

He has been with the Department of Electrical and Computer Engineering, Instituto Superior Técnico, University of Lisbon, since October 1980, where he is currently a Full Professor. Since 1992, he has been on leave with the University of Lisbon and with the Department of Electrical and Computer Engineering, Faculty of Science and Technology, University of Macau, Macau, China, where he has been a Chair-Professor since August 2013. Since July 2010, he has been an Academician with the Lisbon Academy of Sciences, Lisbon. He was the Founding Director of the State Key Laboratory of Analog and Mixed-Signal VLSI, University of Macau, from 2011 to 2022, where he is also the Director of the Institute of Microelectronics. He has authored or coauthored more than 900 publications, including ten books, 12 book chapters, 50 patents, more than 300 articles in scientific journals, and more than 400 in conference proceedings. His research interests include analog and mixed-signal VLSI design.

Prof. Martins received the Author Recognition Award at the 70 years of ISSCC in 2023 as a Top Contributor with more than 50 papers and three Medals from Macau Government in 1999, 2001, and 2021.



Yan Lu (Senior Member, IEEE) received the Ph.D. degree in electronic and computer engineering from The Hong Kong University of Science and Technology (HKUST), Hong Kong, China, in 2013.

In 2014, he joined the State Key Laboratory of Analog and Mixed-Signal VLSI, University of Macau, Macau, China, where he is currently an Associate Professor. He has authored/coauthored more than 150 peer-reviewed technical articles and two books. His research interests include wireless power transfer circuits and systems, high-density integrated power converters, and voltage regulators.

Dr. Lu is serving as a TPC Member for ISSCC and CICC. He was served as an IEEE SCS Distinguished Lecturer (2022–2023). He was a recipient/co-recipient of the NSFC Excellent Young Scientist Fund (Hong Kong-Macau) in 2021, the Macao Science and Technology Award Second Prizes in 2018 and 2020, the IEEE CAS Society Outstanding Young Author Award in 2017, the ISSCC 2017 Takuo Sugano Award for Outstanding Far-East Paper, and the IEEE Solid-State Circuits Society Pre-Doctoral Achievement Award (2013–2014). He has served as a Guest Editor for the IEEE JOURNAL OF SOLID-STATE CIRCUITS (JSSC) in 2022 and 2023, IEEE TRANSACTIONS ON CIRCUITS AND SYSTEMS—I: REGULAR PAPERS in 2019, and the IEEE TRANSACTIONS ON CIRCUITS AND SYSTEMS—II: EXPRESS BRIEFS from 2018 to 2019. He has been serving as a Young Editor for the *Journal of Semiconductors* since 2021.